



GU (General Use) Type SOP Series [1-Channel (Form B) Type]

PhotoMOS RELAYS

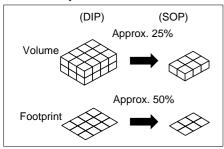


mm inch

FEATURES

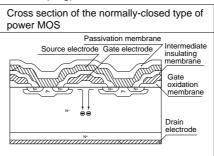
1.1 channel (Form B) in super miniature design

The device comes in a super-miniature SO package measuring (W) $4.4 \times (L)$ $6.3 \times (H)$ 2.1 mm (W) $.173 \times (L)$ $.248 \times (H)$.083 inch —approx. 25% of the volume and 50% of the footprint size of DIP type PhotoMOS Relays.



2. Low on resistance (Max. 50 $\Omega)$ at 400 V for normally-closed type

has been achieved thanks to the built-in MOSFET processed by our proprietary method, DSD (Double-Diffused and Selective Doping) method.



3. Tape and reel

The device comes standard in a tape and reel (1,000 pcs./reel) to facilitate automatic insertion machines.

4. Controls low-level analog signalsPhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

5. Low-level off state leakage current In contrast to the SSR with an off state

leakage current of several milliamps, the PhotoMOS relay features a very small off state leakage current of only 100 pA even at the rated load voltage of 400 V.

6. Low thermal electromotive force (Approx. 1 μ V)

TYPICAL APPLICATIONS

- Telephones
- · Measuring instruments
- Computer
- Industrial robots
- High-speed inspection machines

TYPES

Туре	Output ratings*		Part No.		Packing quantity in
	Load voltage	Load current	Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side	tape and reel
AC/DC	400 V	100 mA	AQV414SX	AQV414SZ	1,000 pcs.

^{*}Indicate the peak AC and DC values.

Notes: (1) Tape package is the standard packing style. Also available in tube. (Part No. suffix "X" ro "Z" is not needed when ordering; Tube: 75 pcs.; Case: 1,500 pcs.)

(2) For space reasons, the top two letters of the product number "AQ" are ommitted on the product seal. The package type indicator "X" and "Z" are also omitted from the seal. (Ex. the label for product number AQV414S is V414S).

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

Item		Symbol	Type of connection	AQV414S	Remarks
Input	LED forward current	İF		50 mA	
	LED reverse voltage	VR		3 V	
	Peak forward current	IFP		1 A	f = 100 Hz, Duty factor = 0.1%
	Power dissipation	Pin		75 mW	
Output	Load voltage (peak AC)	VL		400 V	
	Continuous load current	lι	Α	0.10 A	A connection: Peak AC, DC B,C connection: DC
			В	0.11 A	
			С	0.12 A	
	Peak load current	Ipeak		0.3 A	A connection: 100 ms (1 shot) V _L = DC
	Power dissipation	Pout		450 mW	
Total power dissipation		P⊤		500 mW	
I/O isolation voltage		Viso		1,500 V AC	
Temperature limits	Operating	Topr		-40°C to +85°C -40°F to +185°F	Non-condensing at low temperatures
	Storage	T _{stg}		-40°C to +100°C -40°F to +212°F	

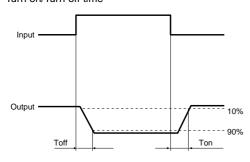
Type of connection.

2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Maximum 3 mA		
Maximum 3 mA	= Max.	
LED turn off current Typical I _{Foff}	12 1110/11	
Typical 0.55 mA	I _I = Max.	
LED dropout voltage $\begin{array}{c ccccc} V_F & - & & & & & & & & & & & & & & & & & $	IL- IVIAX.	
Maximum 1.5 V	I _F = 5 mA	
	= 5 mA	
Manifesture 1.100 1.000	= Max. ithin 1 s on time	
'/	= 5 mA	
Manifesture	= Max. ithin 1 s on time	
· / · · · · · · · · · · · ·	= 5 mA	
	= Max. ithin 1 s on time	
Off state leakage current Maximum I_{Leak} — 1 μ A I_{F}	= 0 = Max.	
Turn on time* Typical Top 0.47 ms IF=	I _F = 5 mA V _L = Max.	
Maximum 1 on 1.0 ms VL:		
Typical Typical 0.28 ms	I _F = 5 mA	
Transfer characteristics Turn off time Toff Maximum Toff Toff Toff Toff Toff Toff Toff Tof	= Max.	
Typical 0.8 pF f =	f = 1 MHz	
I/O capacitance Maximum Ciso - 1.5 pF VB Ciso Ciso	3 = 0	
Initial I/C isolation resistance Minimum R_{iso} — 1,000 $M\Omega$ 500	00 V DC	

Note: Recommendable LED forward current $I_F = 5mA$.

^{*}Turn on/Turn off time

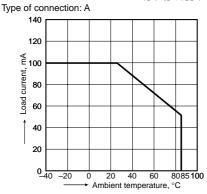


- **■** For Dimensions, see Page 441.
- For Schematic and Wiring Diagrams, see Page 445.
- **■** For Cautions for Use, see Page 449.

REFERENCE DATA

1. Load current vs. ambient temperature characteristics

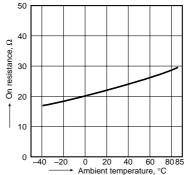
Allowable ambient temperature: -40°C to +85°C -40°F to +185°F



2. On resistance vs. ambient temperature char-

Measured portion: between terminals 4 and 6; LED current: 0 mA;

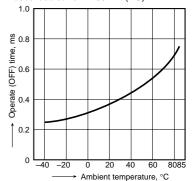
Continuous load current: 100 mA (DC)



3. Operate (OFF) time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: 400 V (DC);

Continuous load current: 100 mA (DC)

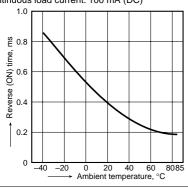


AQV414S

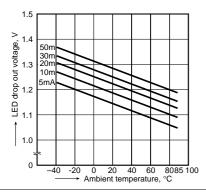
4. Reverse (ON) time vs. ambient temperature characteristics

LED current: 50 mA; Load voltage: 400 V (DC);

Continuous load current: 100 mA (DC)

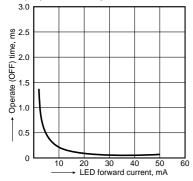


7. LED dropout voltage vs. ambient temperature characteristics LED current: 5 to 50 mA



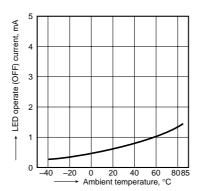
10. LED forward current vs. operate (OFF) time characteristics

Measured portion: between terminals 4 and 6; Load voltage: 400 V (DC); Continuous load current: 100 mA (DC); Ambient temperature: 25°C 77°F



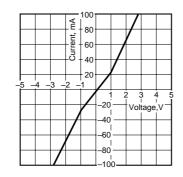
5. LED operate (OFF) current vs. ambient temperature characteristics

Load voltage: 400 V (DC); Continuous load current: 100 mA (DC)



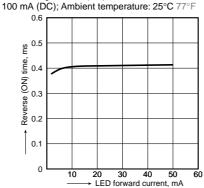
8. Voltage vs. current characteristics of output at MOS portion

Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



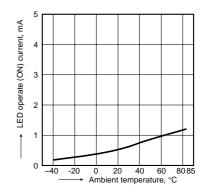
11. LED forward current vs. reverse (ON) time characteristics

Measured portion: between terminals 4 and 6; Load voltage: 400 V (DC); Continuous load current:



6. LED reverse (ON) current vs. ambient temperature characteristics

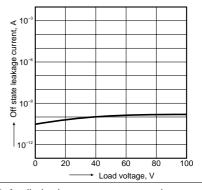
Load voltage: 400 V (DC); Continuous load current: 100 mA (DC)



9. Off state leakage current

Measured portion: between terminals 4 and 6; LED current: 5 mA;

Ambient temperature: 25°C 77°F



12. Applied voltage vs. output capacitance characteristics

Measured portion: between terminals 4 and 6;

Frequency: 1 MHz; Ambient temperature: 25°C 77°F

120 造100 Output capacitance 80 60 40 20 10 20 30 40 50 Applied voltage, V